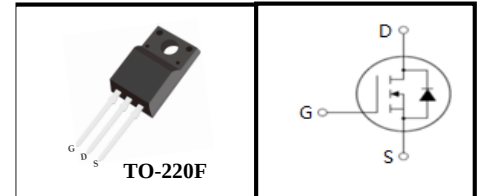


FEATURES

- $BV_{DSS}=650V$, $I_D=20A$
- $R_{DS(on)}:0.17\Omega(Max)@V_{GS}=10V$
- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Ordering code	Package	Marking
MPSA65M170	TO-220F	MP65M170

Absolute Maximum Ratings $T_C = 25^\circ C$, unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-220F	
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	650	V
Continuous Drain Current	I_D	20	A
Pulsed Drain Current (note1)	I_{DM}	60	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	480	mJ
Avalanche Current (note1)	I_{AR}	3.5	A
Repetitive Avalanche Energy (note1)	E_{AR}	0.7	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0 \dots 400V$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0 \dots 400V$, $I_{SD} \leq I_D$	dv/dt	50	V/ns
Power Dissipation ($T_C = 25^\circ C$)	P_D	34	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ C$

Thermal Resistance			
Parameter	Symbol	Value	Unit
		TO-220F	
Thermal Resistance, Junction-to-Case	R_{thJC}	4	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	650	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 650V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
		V _{DS} = 650V, V _{GS} = 0V, T _J = 150°C	--	--	100	
Gate-Source Leakage	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 0.25mA	2.5	--	3.5	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 10A	--	0.14	0.17	Ω
Gate Resistance	R _G	f = 1.0MHz, open drain	--	8	--	Ω
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 100V, f = 1.0MHz	--	1724	--	pF
Output Capacitance	C _{oss}		--	72	--	
Reverse Transfer Capacitance	C _{rss}		--	6	--	
Total Gate Charge	Q _g	V _{DD} = 400V, I _D = 20A, V _{GS} = 10V	--	38.5	--	nC
Gate-Source Charge	Q _{gs}		--	8	--	
Gate-Drain Charge	Q _{gd}		--	15	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 400V, I _D = 20A, V _{GS} = 10V, R _G = 25Ω	--	25	--	ns
Turn-on Rise Time	t _r		--	59	--	
Turn-off Delay Time	t _{d(off)}		--	121	--	
Turn-off Fall Time	t _f		--	44	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	20	A
Pulsed Diode Forward Current	I _{SM}		--	--	60	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 20A, V _{GS} = 0V	--	0.9	1.2	V
Reverse Recovery Time	t _{rr}	V _R = 400V, I _F = 20A, di _F /dt = 100A/μs	--	453	--	ns
Reverse Recovery Charge	Q _{rr}		--	5.1	--	μC
Peak Reverse Recovery Current	I _{rrm}		--	22	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 3.5A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

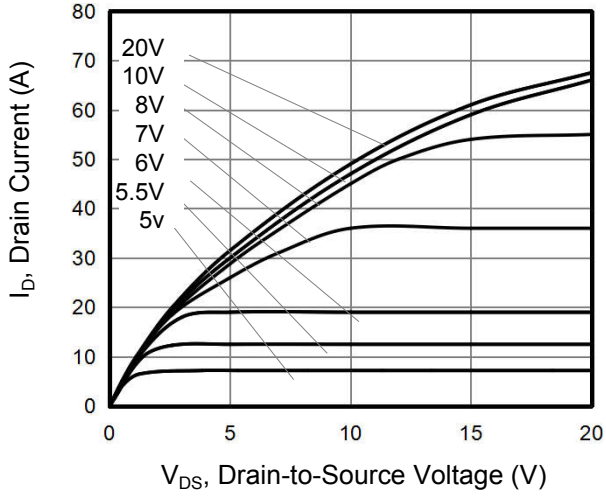


Figure 2. Transfer Characteristics

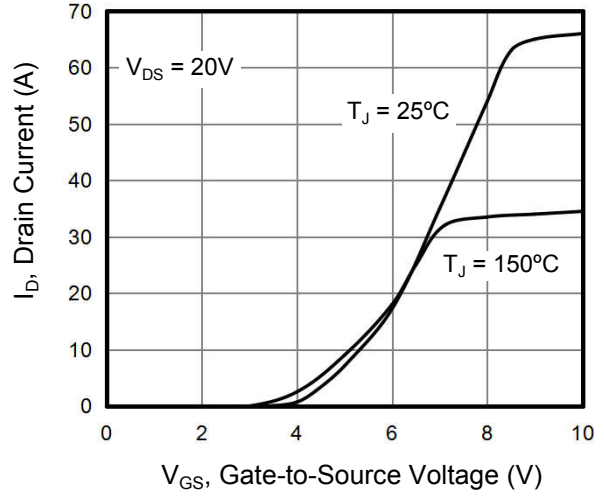


Figure 3. On-Resistance vs. Drain Current

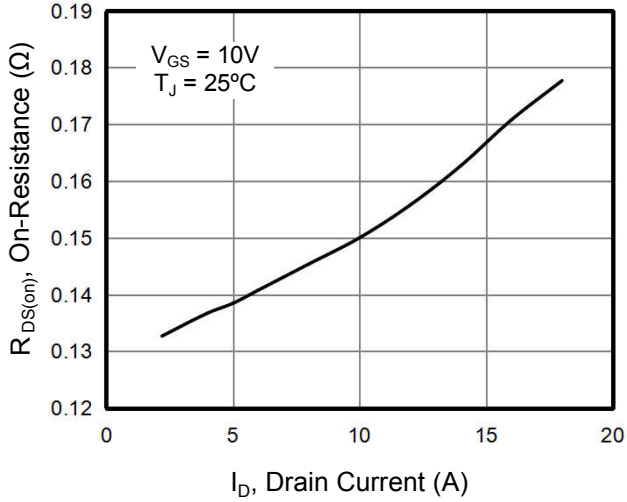


Figure 4. Capacitance

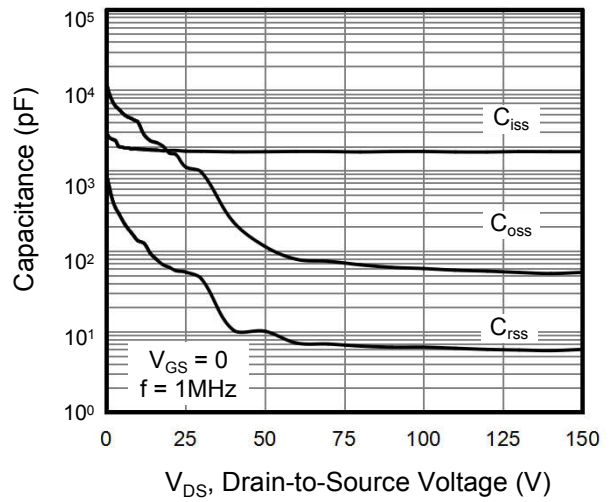


Figure 5. Gate Charge

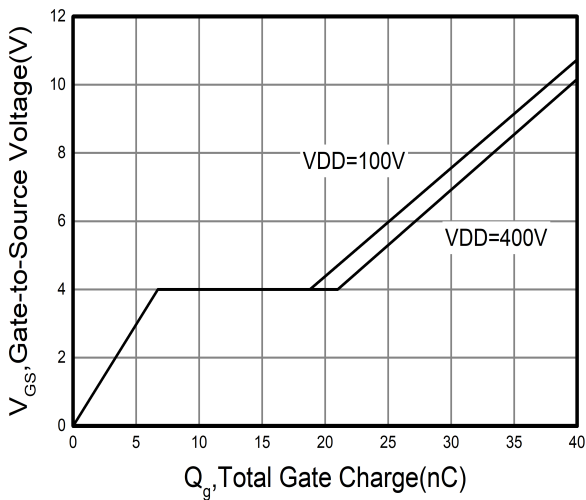
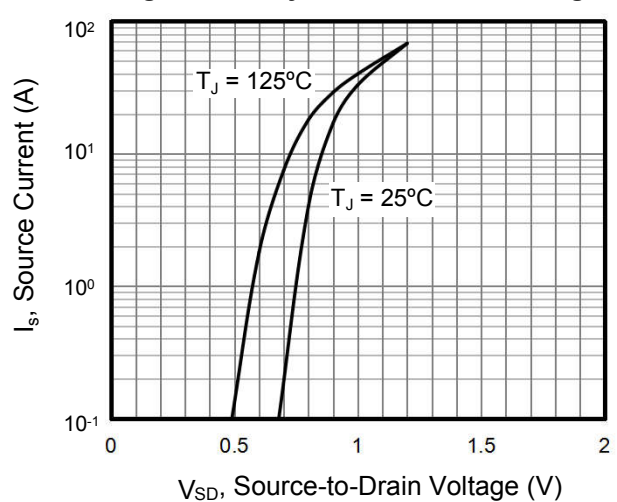


Figure 6. Body Diode Forward Voltage



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

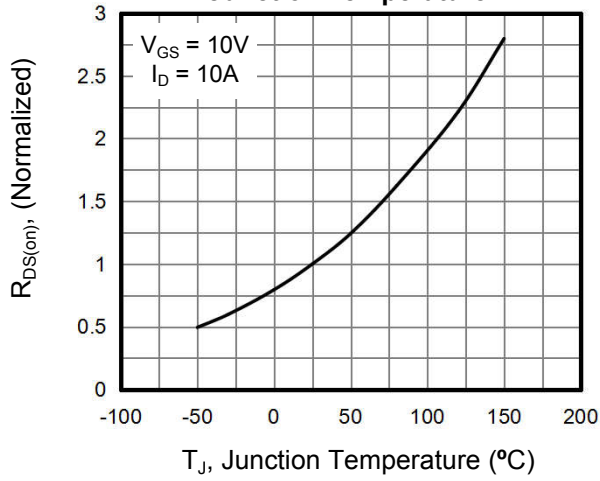


Figure 8. Threshold Voltage vs. Junction Temperature

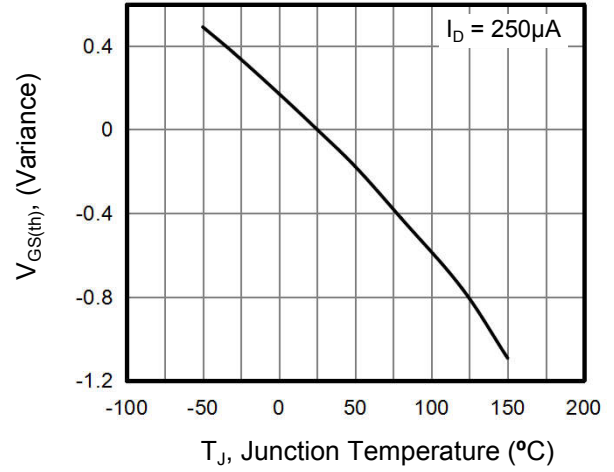


Figure 9. Transient Thermal Impedance

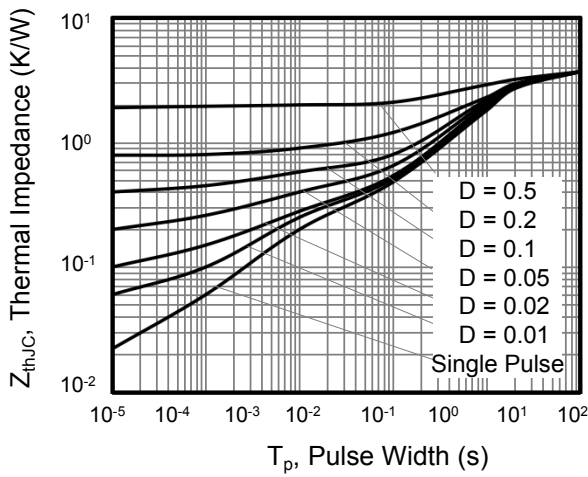


Figure A: Gate Charge Test Circuit and Waveform

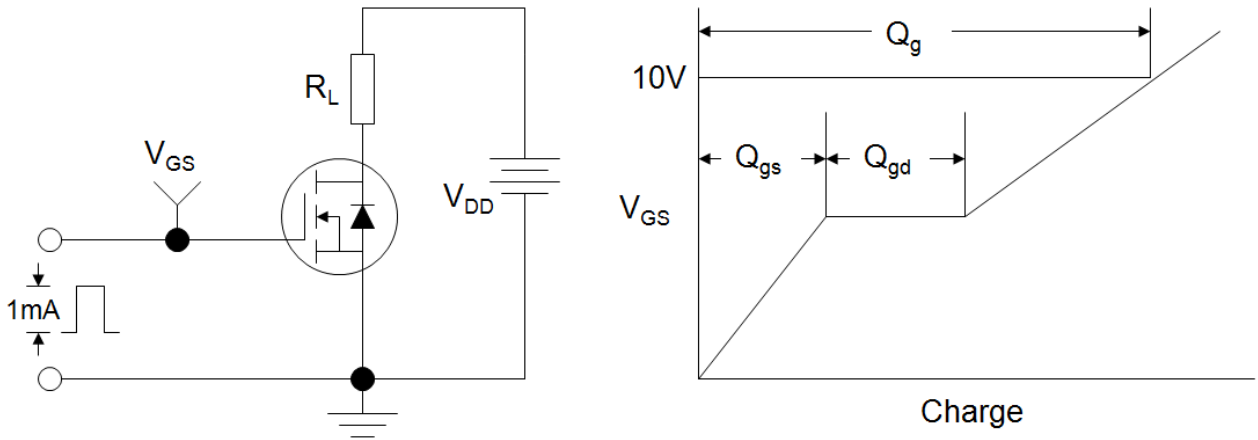


Figure B: Resistive Switching Test Circuit and Waveform

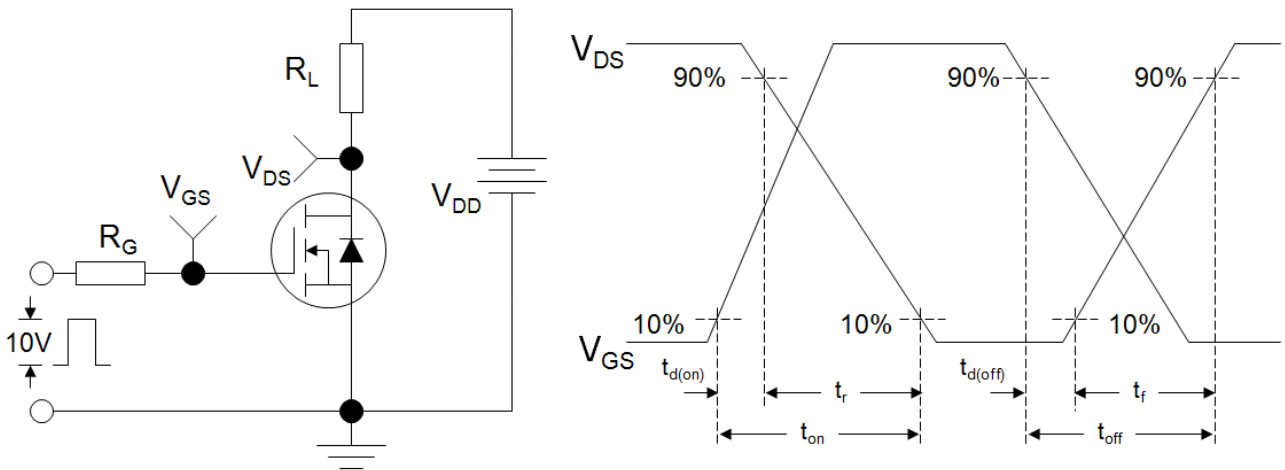
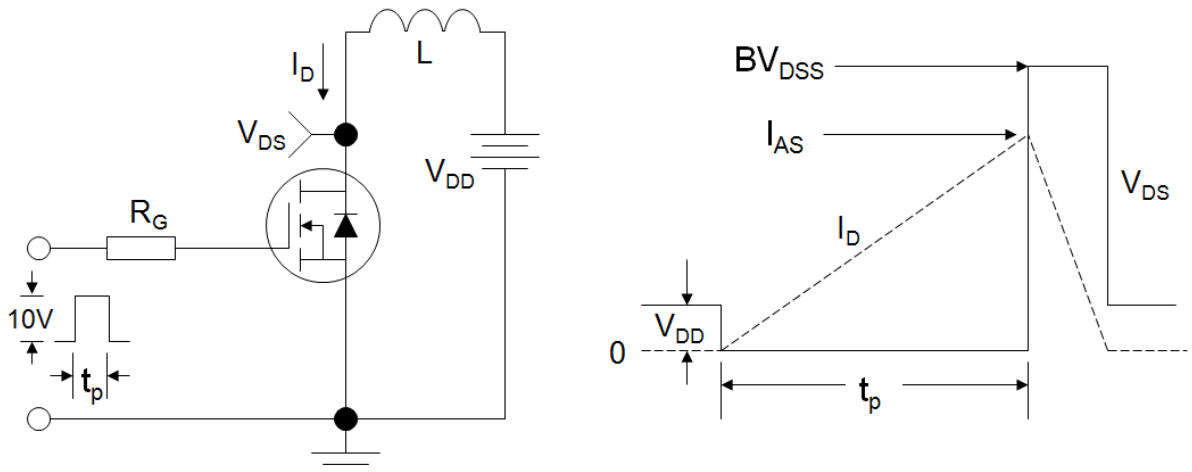
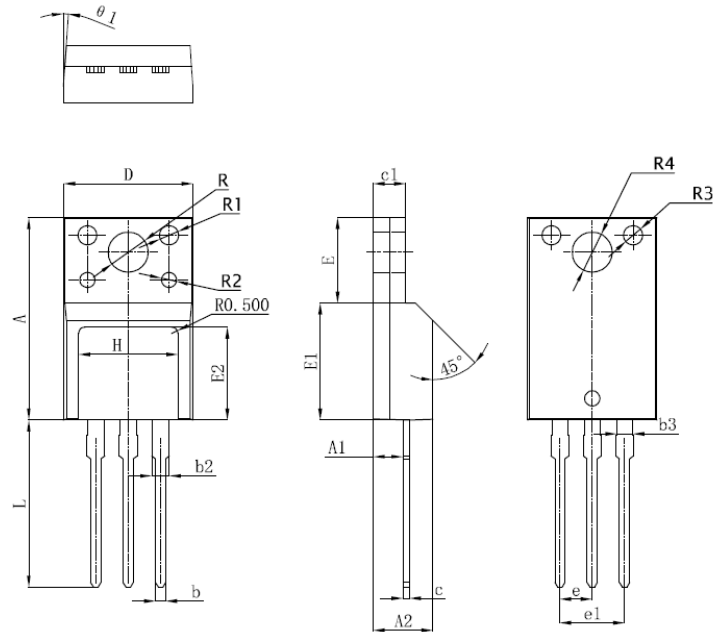


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



TO-220F



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.670	15.870	16.070
A1	2.150	2.350	2.550
A2	4.500	4.700	4.900
b	0.770	0.800	0.830
b2	1.200	1.300	1.400
b3	1.200BSC		
c	0.490	0.500	0.520
c1	2.340	2.540	2.740
D	9.960	10.160	10.360
E	6.480	6.680	6.880
E1	8.990	9.190	9.390
E2	7.100	7.300	7.500
e	2.540BSC		
e1		5.080	
L	13.140	13.340	13.540
R		3.150	
R1		1.500	
R2		1.200	
R3		1.500	
R4		3.180	
H	7.600	7.800	8.000
θ 1	4°	4.5°	5°